Docket No.

248442US0

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Toshiya SAGISAKA, et al.

SERIAL NO: NEW APPLICATION

GAU:

FILED:

HEREWITH

EXAMINER:

FOR:

NEW ARYL AMINE POLYMER, THIN FILM TRANSISTOR USING THE NEW ARYL AMINE POLYMER,

AND METHOD OF MANUFACTURING THE THIN FILM TRANSISTOR

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number <u>15-0030</u>. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,

MAIER & NEUSTADT, P.C.

J. Derek Mason, Ph. D.

Registration No. 35,270

Customer Number

22850

Tel. (703) 413-3000 Fax. (703) 413-2220 (OSMMN 05/03)

LIST OF RELATED CASES

Docket Number	Serial or Patent Number	Filing or Issue Date	Inventor/ Applicant
194076US0	09/610,427	07/05/00	RI, et al.
			,
218335US0 CONT	10/051,230	01/22/02	RI, et al.
205260US0	6,492,079	12/10/02	SHIMADA, et al.
209798US0	6,596,449	07/22/03	SHIMADA, et al.
PER CLIENT	4,892,949	01/09/90	SASAKI
PER CLIENT	4,859,556	08/22/89	SASAKI
0557-3873-0X	5,840,454	11/24/98	NAGAI, et al.
0557-4344-0X DIV	6,018,014	01/25/00	NAGAI, et al.
0557-4734-0	6,187,494	02/13/01	KAWAMURA, et al.
198421US0-DIV	6,303,736	10/16/01	KAWAMURA, et al.

Form PTO 1449 U.S. DEPARTMENT OF COMMERCE (Modified) PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO.		SERIAL NO.				
		248442US0	NEW APPLICATION					
				APPLICANT				
LIST OF I	REFE	RENCES CITED BY AP	PLICANT	Toshiya SAGISAKA, et al.				
			•	FILING DATE		GROUP		
				HEREWITH				
				U.S. PATENT DOCUMENTS				
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS		LING DATE PPROPRIATE
	AA	6,492,079	12/10/02	SHIMADA, ET AL.				
	AB	6,596,449	07/22/03	SHIMADA, ET AL.				
	AC	4,892,949	01/09/90	SASAKI .				
	AD	4,859,556	08/22/89	SASAKI				
	AE	5,840,454	11/24/98	NAGAI, ET AL.				
	AF	6,018,014	01/25/00	NAGAI, ET AL.			-	
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	AJ	10-310635	11/24/98	JAPAN / w abstract				,,,,
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	AL	08-228034	09/03/96	JAPAN / w abstract				
	AM	08/228035	09/03/96	JAPAN / w abstract	*			
	AN	11-195790	07/21/99	JAPAN / w abstract				
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	AP	58-198043	11/17/83	JAPAN / w abstract				
	AQ	60-098437	06/01/85	JAPAN / w abstract	· · · · · · · · · · · · · · · · · · ·			
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I		OTHER RI	FERENCES /	Including Author, Title, Date, Pertine	ont Pages o	to \		
<u> </u>				nd photoconducting polyarylenevinylene			phenyle	ene arylamine and
_	AV	phenylene oxide units	in the main ch	ain, Synthetic Metals 84, pp. 269-270,	1997.			·
	AW	R.C. Haddon, et al., C	60 thin film tran	sistors, Appl. Phys. Lett 67 (1), 3 July	1995, pp. 12 [.]	1-123		
	AX	Zhenan Bao, et al., Or Physics, pp. 3066-306		ect transistors with high mobility based	on copper pl	nthalocyani	ne, Ame	erican Institute of
	AY	Zhenan Bao, et al, Soluble and processable regioregular poly (3-hexylthiophene) for thin film filed-efect transistor applications with high mobility., American Institute of Physics, pp., 4108-4110, 1996.					sheet(s) attached	
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LIST OF REFERENCES CITED BY APPLICANT		Toshiya S	AGISAKA, et al.			
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AAA	H. Sirringhaus, et al., Bis(dithienothic Physics, pp. 3871-3873, 1997.	ophene) organic field-effect transistors wi	th a high ON/OFF ration., American Institute of			
AAB	Howard E. Katz, et al., a,a-Dihexylqu Materials, Volume 10, Number 2, pp.	et al., a,a-Dihexylquaterthiophene: A Second Thin Film Single-Crystal Organic Semiconductor, Chemistry of e 10, Number 2, pp., 457-459, February 1998.				
AAC	Gilles Horowitz, et al., Role of the semiconductor/insulator interface in the characteristics of π -conjugated-oligomer-based thin-film transistors, Synthetic Metals, 51, pp. 419-424, 1992.					
AAD	H. Fuchigami, et al., Polythienylene thin-film transistor with high carrier mobility, American Institute of Physics, Appl. Phys. Lettt. 63, (10), 6 September 1993.					
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AAF	H. Sirringhaus, et al., High-Resolution Inkjet Printing of All-Polymer Transistor Circuits, Science Vol 290, PP., 2123-2126, December 2000.					
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Examiner			Date Considered			
*Examiner: Initial if conformance and no	reference is considered, whether or not considered. Include copy of this form	t citation is in conformance with MPEP 60 with next communication to applicant.	99; Draw line through citation if not in			